



22. (Amended) A process for the production of a supported electrochemical transistor device comprising:

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- forming a source contact,
 - forming a drain contact,
 - forming at least one gate electrode,
 - forming an electrochemically active element arranged between, and in direct electrical contact with the source and drain contacts, wherein said electrochemically active element comprises a transistor channel and is of a material comprising an organic material having the ability of electrochemically altering its conductivity through change of redox state thereof, and
 - forming a solidified electrolyte in direct electrical contact with the electrochemically active element and said at least one gate electrode and interposed between them in such a way that electron flow between the electrochemically active element and said gate electrode(s) is prevented,

wherein said contacts, electrode(s), electrochemically active element and electrolyte are deposited directly onto a support.



25. (Twice Amended) A process according to claim 22, in which said organic material comprises a polymer, wherein said polymer is deposited on the support through *in situ* polymerisation.

29. (Amended) A process according to claim 26, in which said patterning is performed by mechanical means selected from the group consisting of scratching, scoring, scraping and milling.

32. (Amended) A process according to claim 23, in which said organic material comprises a polymer, wherein said polymer is deposited on a support through *in situ* polymerisation.

33. (Amended) A process according to claim 24, in which said organic material comprises a polymer, wherein said polymer is deposited on a support through *in situ* polymerisation.
